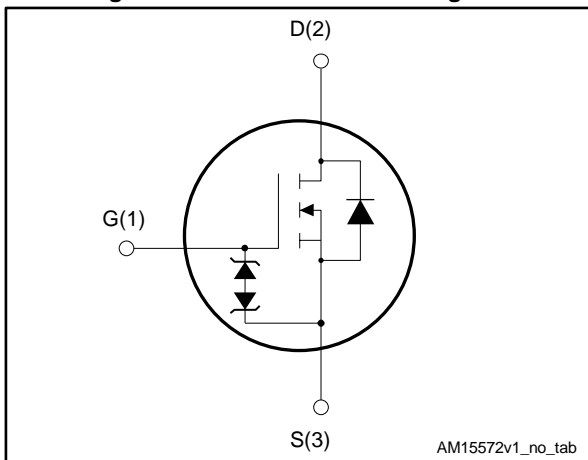


## N-channel 650 V, 0.6 $\Omega$ typ., 10 A SuperMESH™ Power MOSFET in a TO-220FP package

Datasheet - production data



Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max.	I <sub>D</sub>	P <sub>TOT</sub>
STF12NK65Z	650 V	0.7 $\Omega$	10 A	35 W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Zener-protected

### Applications

- Switching applications

### Description

This high voltage device is a Zener-protected N-channel Power MOSFET developed using the SuperMESH™ technology by STMicroelectronics, an optimization of the well-established PowerMESH™. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.

Table 1: Device summary

Order code	Marking	Package	Packaging
STF12NK65Z	12NK65Z	TO-220FP	Tube

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## Contents

<b>1</b>	<b>Electrical ratings .....</b>	<b>3</b>
<b>2</b>	<b>Electrical characteristics .....</b>	<b>4</b>
	2.1 Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits .....</b>	<b>8</b>
<b>4</b>	<b>Package information .....</b>	<b>9</b>
	4.1 TO-220FP package information .....	10
<b>5</b>	<b>Revision history .....</b>	<b>12</b>

# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source voltage	650	V
V <sub>GS</sub>	Gate-source voltage	±30	V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	10	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 100 °C	6.3	A
I <sub>DM</sub> <sup>(1)</sup>	Drain current (pulsed)	40	A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	35	W
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T <sub>C</sub> = 25 °C)	2500	V
dv/dt <sup>(2)</sup>	Peak diode recovery voltage slope	4.5	V/ns
T <sub>stg</sub>	Storage temperature range	-55 to 150	°C
T <sub>j</sub>	Operation junction temperature range		

**Notes:**

<sup>(1)</sup>Pulse width limited by safe operating area

<sup>(2)</sup>I<sub>SD</sub> ≤ 10 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case	3.6	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient	62.5	°C/W

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
I <sub>AR</sub>	Avalanche current, repetitive or non-repetitive (pulse width limited by T <sub>JMAX</sub> )	10	A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>J</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	225	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5: On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ , $I_D = 1\text{ mA}$	650			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 650\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 650\text{ V}$ , $T_C = 125\text{ °C}^{(1)}$			50	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 100\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on- resistance	$V_{GS} = 10\text{ V}$ , $I_D = 10\text{ A}$		0.6	0.7	$\Omega$

**Notes:**

<sup>(1)</sup>Defined by design, not subject to production test.

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$	-	1837	-	pF
$C_{oss}$	Output capacitance		-	208	-	pF
$C_{rss}$	Reverse transfer capacitance		-	48.8	-	pF
$C_{oss\ eq}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ to }520\text{ V}$	-	122	-	pF
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 10\text{ A}$ , $V_{GS} = 0\text{ to }10\text{ V}$ (see <a href="#">Figure 15: "Test circuit for gate charge behavior"</a> )	-	62.6	-	nC
$Q_{gs}$	Gate-source charge		-	9.6	-	nC
$Q_{gd}$	Gate-drain charge		-	36	-	nC
$R_G$	Intrinsic gate resistance		$f = 1\text{ MHz}$ , $I_D = 0\text{ A}$	-	1	-

**Notes:**

<sup>(1)</sup> $C_{oss\ eq}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325 \text{ V}$ , $I_D = 5 \text{ A}$ , $R_G = 4.7 \text{ } \Omega$ , $V_{GS} = 10 \text{ V}$ (see <a href="#">Figure 14: "Test circuit for resistive load switching times"</a> and <a href="#">Figure 19: "Switching time waveform"</a> )	-	25	-	ns
$t_r$	Rise time		-	14	-	ns
$t_{d(off)}$	Turn-off delay time		-	55	-	ns
$t_f$	Fall time		-	11.5	-	ns

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		10	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		40	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 10 \text{ A}$ , $V_{GS} = 0 \text{ V}$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 10 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 16: "Test circuit for inductive load switching and diode recovery times"</a> )	-	436		ns
$Q_{rr}$	Reverse recovery charge		-	3.4		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	$I_{SD} = 10 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 60 \text{ V}$ , $T_J = 150 \text{ }^\circ\text{C}$ (see <a href="#">Figure 16: "Test circuit for inductive load switching and diode recovery times"</a> )	-	15.4		A
$t_{rr}$	Reverse recovery time		-	518		ns
$Q_{rr}$	Reverse recovery charge		-	4.1		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	15.9		A

**Notes:**(1) Pulsed: pulse duration=300  $\mu\text{s}$ , duty cycle 1.5%.

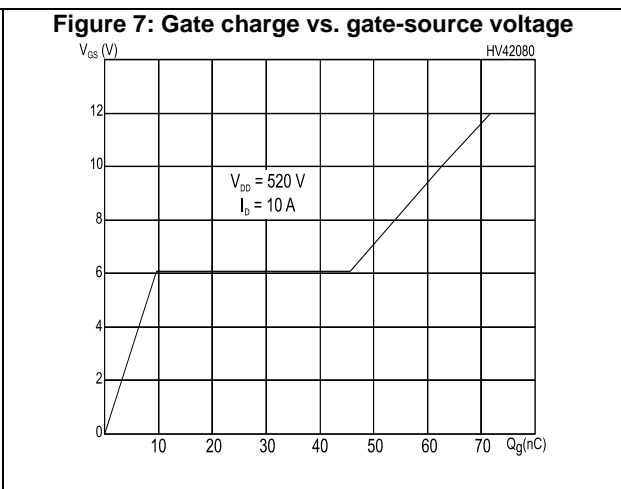
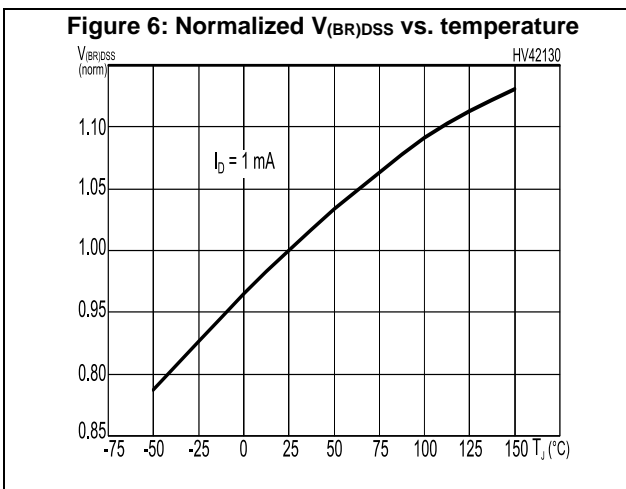
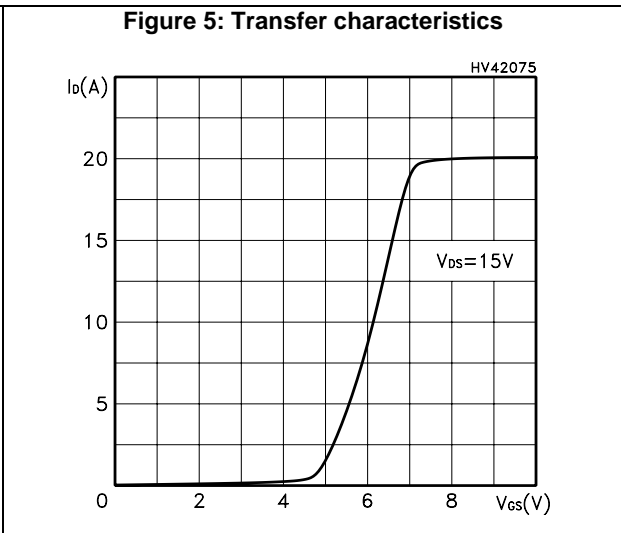
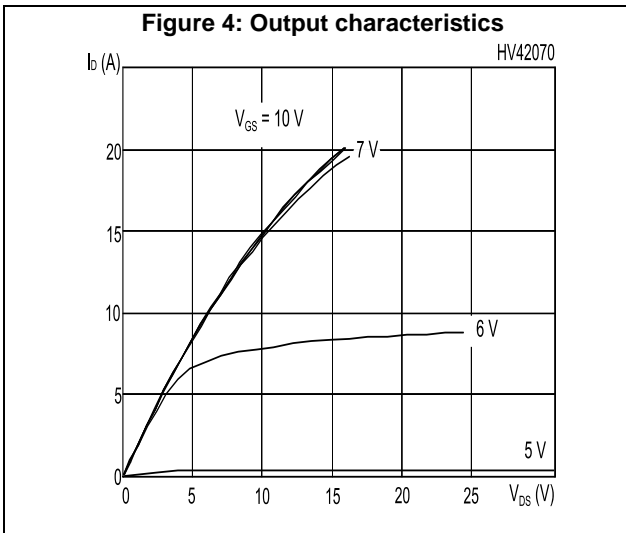
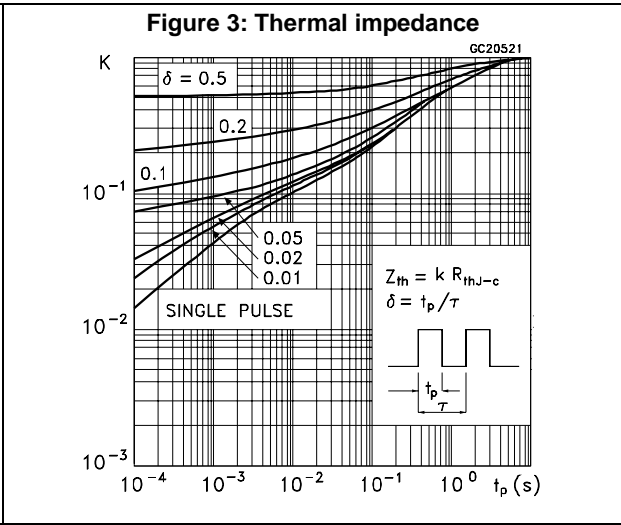
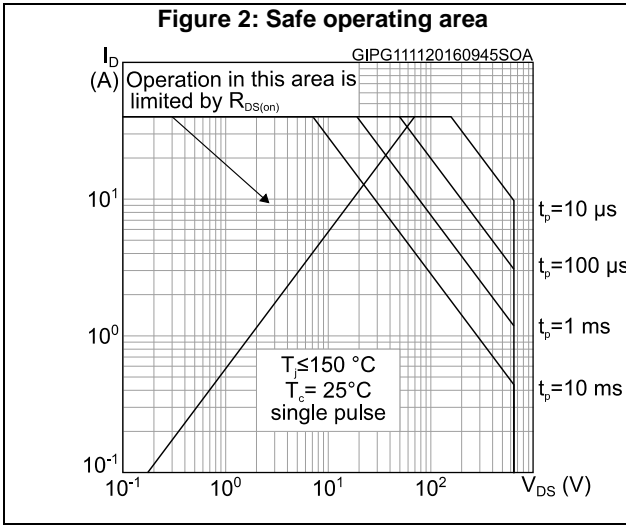
(2) Pulse width limited by safe operating area.

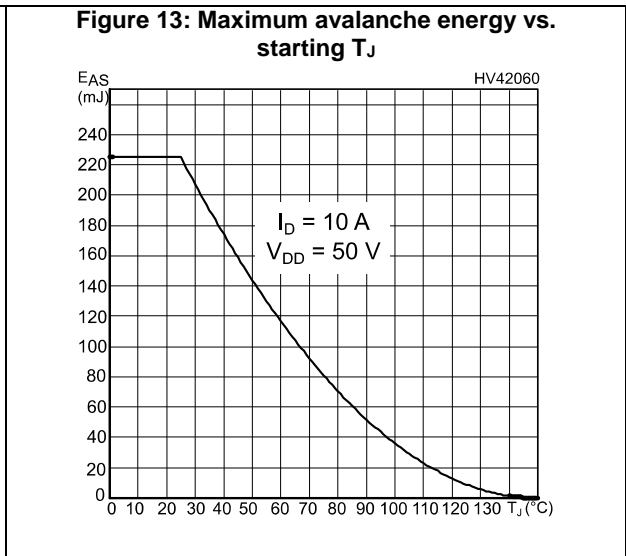
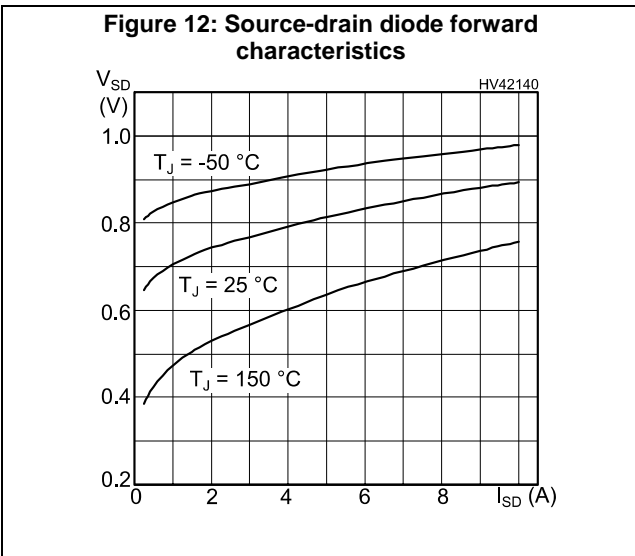
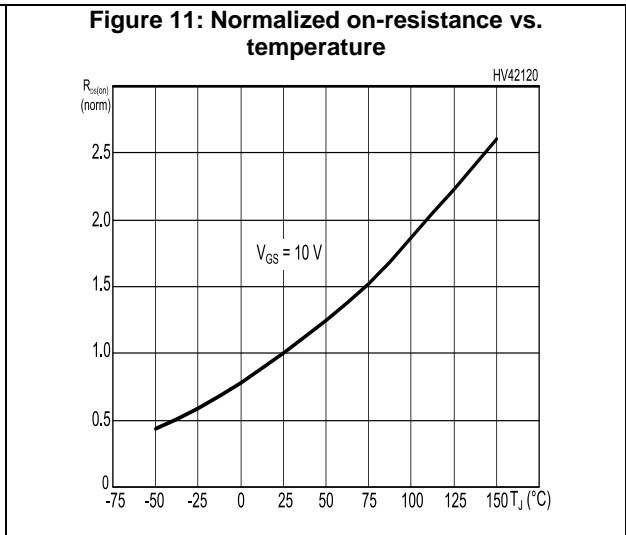
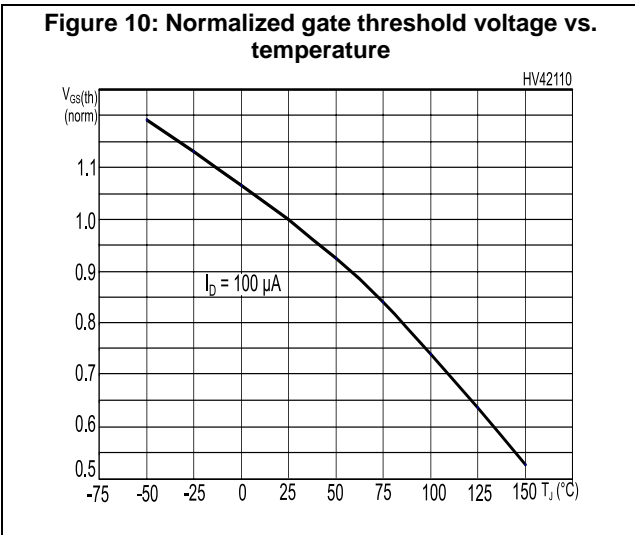
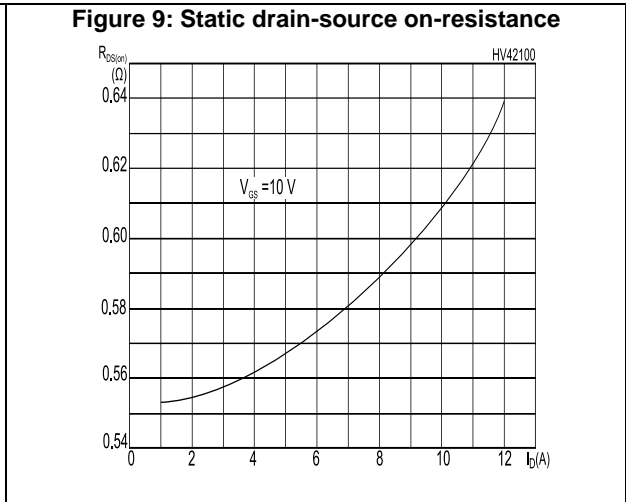
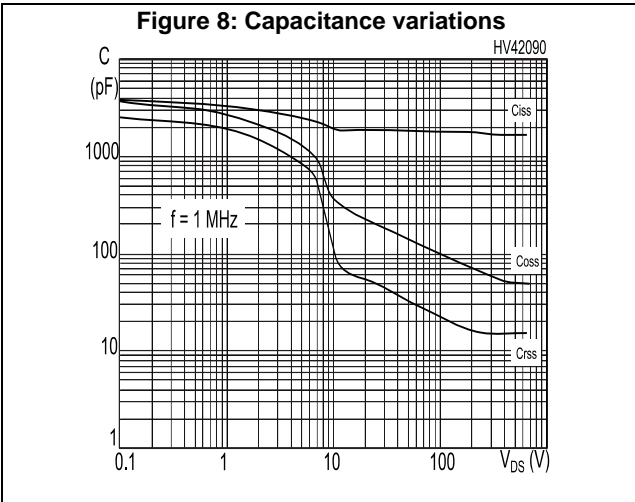
Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1 \text{ mA}$ , $I_D = 0 \text{ A}$	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

### 2.1 Electrical characteristics (curves)





### 3 Test circuits

**Figure 14: Test circuit for resistive load switching times**



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**Figure 15: Test circuit for gate charge behavior**



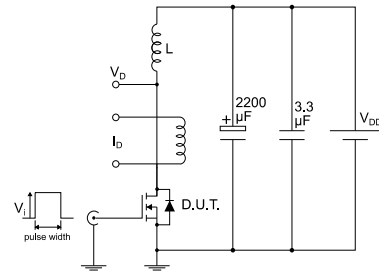
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**Figure 16: Test circuit for inductive load switching and diode recovery times**



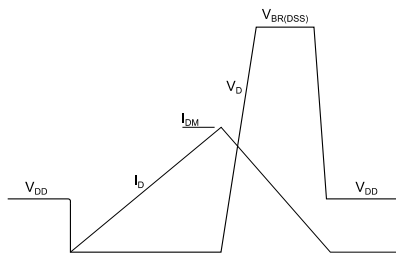
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**Figure 17: Unclamped inductive load test circuit**



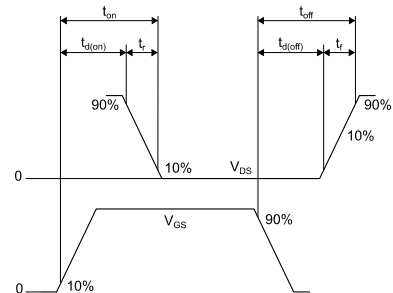
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**Figure 18: Unclamped inductive waveform**



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**Figure 19: Switching time waveform**



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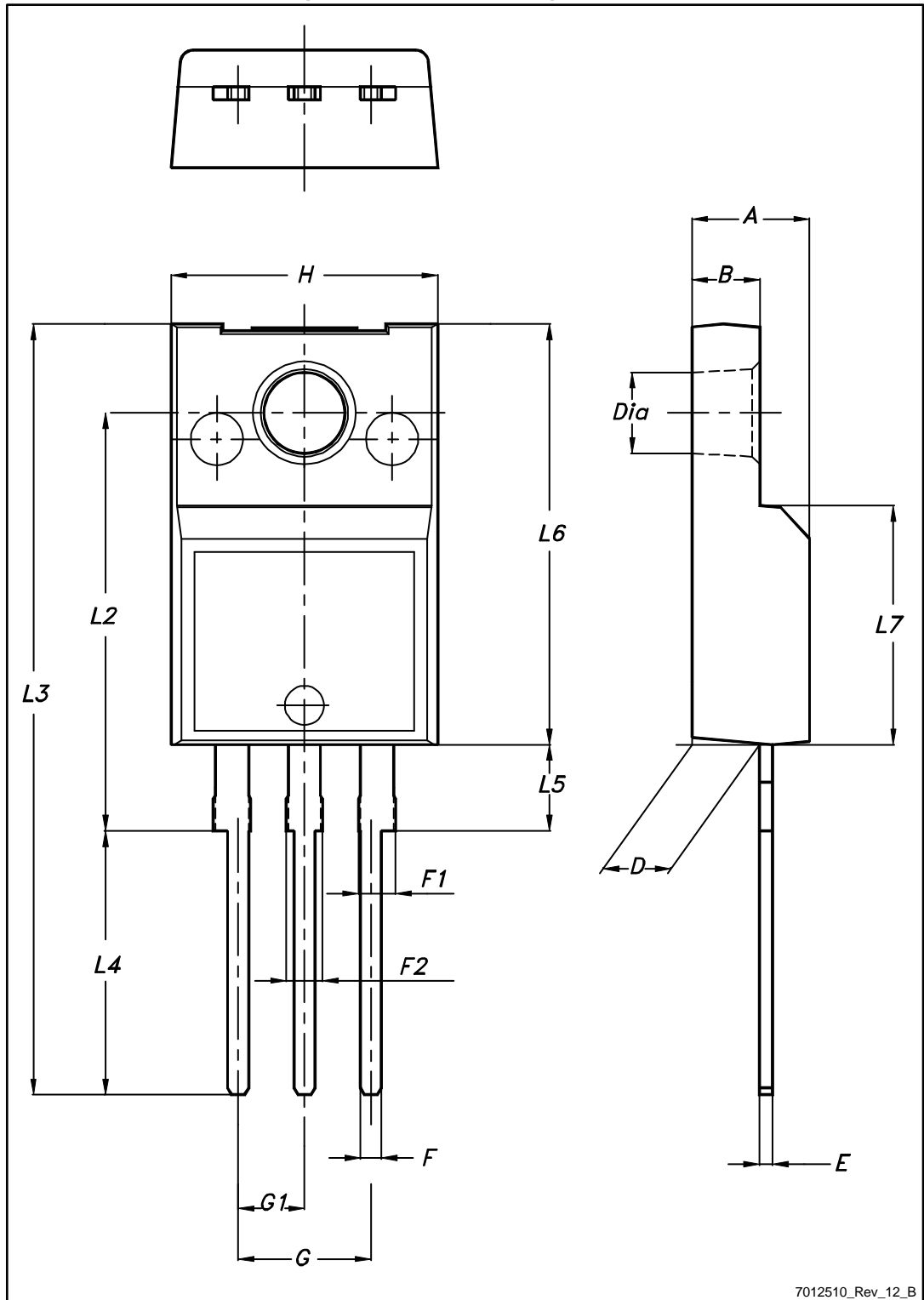


## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO-220FP package information

Figure 20: TO-220FP package outline



7012510\_Rev\_12\_B

Table 10: TO-220FP package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

## 5 Revision history

**Table 11: Document revision history**

Date	Revision	Changes
01-Oct-2010	1	Initial release.
10-Nov-2016	2	Modified title, features and description in cover page Modified <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 3: "Thermal data"</i> , <i>Table 5: "On /off states"</i> , <i>Table 6: "Dynamic"</i> , <i>Table 8: "Source drain diode"</i> , <i>Table 9: "Gate-source Zener diode"</i> Modified <i>Figure 2: "Safe operating area"</i> Updated <i>Section 4.1: "TO-220FP package information"</i> Minor text changes
05-Apr-2017	3	Datasheet status promoted from preliminary to production data. Updated <a href="#">Section 2.1: "Electrical characteristics (curves)"</a> . Minor text changes

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